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In the Claims:

1 1. (Currently amended) A method of fabricating a semiconductor
2 device by employing ion implantation to provide a
3 SiC semiconductor substrate at a surface thereof with a
4 region having dopant introduced therein, comprising the
5 steps of: providing said semiconductor substrate at least
6 at a first region of a surface thereof with a mask layer
7 including a polyimide resin film; and implanting dopant
8 ions to an implantation depth into said semiconductor
9 substrate at a second region of said surface of said
10 semiconductor substrate free of said polyimide resin film;
11 wherein said polyimide resin film has a thickness of at
12 least twice said implantation depth.

Claims 2 to 5 (Canceled).

1 6. (Previously presented) The method of claim 1, wherein said
2 semiconductor substrate is heated to at least 300°C and
3 said dopant ions are implanted.

1 7. (Previously presented) The method of claim 1, wherein said
2 semiconductor substrate is heated to at least 500°C and
3 said dopant ions are implanted.

1 8. (Previously presented) The method of claim 1, wherein said
2 polyimide resin film is formed of photosensitive polyimide
3 resin.

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Claim 9 (Canceled).

1 10. (Previously presented) The method of claim 1, wherein a
2 thin metal film is further interposed between said
3 polyimide resin film and said semiconductor substrate.

1 11. (Previously presented) The method of claim 1, wherein a
2 thin film formed of SiO₂ is further interposed between said
3 polyimide resin film and said semiconductor substrate.

Claims 12 to 24 (Canceled).

1 25. (Previously presented) The method of claim 1, wherein said
2 mask layer is deposited on said semiconductor substrate at
3 said first region to be undoped with said dopant ions.

1 26. (Currently amended) The method of claim 1, wherein said
2 dopant ions are implanted into ~~[[a]]~~ said second region
3 unmasked which is not masked by said mask layer.

1 27. (Currently amended) A method of preparing a doped
2 semiconductor substrate, comprising the steps:
3 a) providing a semiconductor substrate comprising SiC;
4 b) providing a mask layer including a polyimide resin
5 film that consists of a photosensitive polyimide resin
6 on a first region of a surface of said substrate, by
7 applying said polyimide resin film on said first

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8 region and a second region of said surface, then
9 exposing said polyimide resin film to light at said
10 first region, and then removing said polyimide resin
11 film at said second region, wherein said step b) does
12 not involve photolithography employing a photoresist;
13 c) heating said substrate to at least 300°C; and
14 d) while said substrate is at least 300°C, implanting, by
15 ion implantation, dopant ions into said substrate
16 through ~~[[a]]~~ said second region of said surface to
17 form in said substrate a doped region that is doped
18 with said dopant ions- ions;
19 wherein said method does not involve chemical vapor
20 deposition and does not involve dry etching.

Claim 28 (Canceled).

1 29. (Previously presented) The method according to claim 27,
2 further comprising, after said step d), a step of removing
3 said polyimide resin film by wet etching using hydrofluoric
4 acid.

1 30. (Currently amended) ~~The method according to claim 27,~~
2 A method of preparing a doped semiconductor substrate,
3 comprising the steps:
4 a) providing a semiconductor substrate comprising SiC;
5 b) providing a mask layer including a polyimide resin
6 film on a first region of a surface of said substrate;
7 c) heating said substrate to at least 300°C; and

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8 d) while said substrate is at least 300°C, implanting, by
9 ion implantation, dopant ions into said substrate
10 through a second region of said surface to form in
11 said substrate a doped region that is doped with said
12 dopant ions;

13 wherein said polyimide resin film has a thickness of at
14 least twice a depth of said doped region.

1 31. ~~(Currently amended) The method according to claim 27,~~
2 A method of preparing a doped semiconductor substrate,
3 comprising the steps:

4 a) providing a semiconductor substrate comprising SiC;
5 b) providing a mask layer including a polyimide resin
6 film on a first region of a surface of said substrate;
7 c) heating said substrate to at least 300°C; and
8 d) while said substrate is at least 300°C, implanting, by
9 ion implantation, dopant ions into said substrate
10 through a second region of said surface to form in
11 said substrate a doped region that is doped with said
12 dopant ions;

13 wherein said step b) further comprises forming said mask
14 layer to include a metal film interposed between said
15 polyimide resin film and said substrate.

1 32. ~~(Currently amended) The method according to claim 27,~~
2 A method of preparing a doped semiconductor substrate,
3 comprising the steps:

4 a) providing a semiconductor substrate comprising SiC;

5 b) providing a mask layer including a polyimide resin
6 film on a first region of a surface of said substrate;
7 c) heating said substrate to at least 300°C; and
8 d) while said substrate is at least 300°C, implanting, by
9 ion implantation, dopant ions into said substrate
10 through a second region of said surface to form in
11 said substrate a doped region that is doped with said
12 dopant ions;

13 wherein said step b) further comprises forming said mask
14 layer to include a SiO_2 film interposed between said
15 polyimide resin film and said substrate.

[RESPONSE CONTINUES ON NEXT PAGE]